



Figure 1: FTIR results for B_2O_3 spontaneous etching. B_2O_3 films were first grown using B_2O_3 ALD. B_2O_3 films were then etched using sequential HF exposures. Each HF exposure was performed for 1 s at 0.1 Torr and $200^\circ C$.

Figure 2: QMS results for volatile etch products during B_2O_3 spontaneous etching using B_2O_3 nanopowder. B_2O_3 was etched with HF exposure. HF exposure was performed for 60 s at 9 Torr and $200^\circ C$.